

**IN THE CLAIMS:**

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1. (Currently Amended): A semiconductor device comprising:

a capacitor formed above a semiconductor substrate and including

a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,

a capacitor dielectric film formed on the storage electrode, and

a plate electrode formed on the capacitor dielectric film,

an upper cylinder edge of the storage electrode the edge of the cylindrical projection being  
rounded and having a larger thickness than a thickness in the a rest portion. 1/ 2

2. (Currently Amended): A semiconductor device according to claim 1, wherein

the cylindrical-shaped storage electrode has a thickness gradually thickened toward to the upper cylinder edge the edge of the cylindrical projection.

3. (Currently Amended): A semiconductor device according to claim 1, wherein

a side surface of the storage electrode cylindrical projection is tilted and a peripheral circumferential  
length of a cylinder the cylindrical projection is gradually increased toward to the upper cylinder edge the edge of the cylindrical projection.

4. (Currently Amended): A semiconductor device according to claim 2, wherein  
a side surface of the storage electrode cylindrical projection is tilted and a peripheral circumferential  
length of ~~a cylinder~~ the cylindrical projection is gradually increased toward ~~to the upper cylinder edge~~ the  
edge of the cylindrical projection.

B'  
5-6. (Canceled)

7. (Currently Amended): A semiconductor device according to claim 1, wherein  
~~an inner surface of the storage electrode at a border portion between a side surface and a bottom~~  
surface of the cylindrical-shaped storage electrode is rounded.

8. (Currently Amended): A semiconductor device according to claim 2, wherein  
~~an inner surface of the storage electrode at a border portion between a side surface and a bottom~~  
surface of the cylindrical-shaped storage electrode is rounded.

9. (Currently Amended): A semiconductor device comprising:  
a capacitor formed above a semiconductor substrate and including  
a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the  
cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,

a capacitor dielectric film formed on the storage electrode, and  
a plate electrode formed on the capacitor dielectric film,  
the cylindrical-shaped storage electrode being formed of a metal film and having a larger  
thickness at ~~an upper cylinder edge~~ the edge of the cylindrical projection than a thickness in a rest portion.

what's that?

10. (Currently Amended): A semiconductor device according to claim 9, wherein  
the cylindrical-shaped storage electrode has a thickness gradually thickened toward ~~to the upper~~  
~~cylinder edge~~ the edge of the cylindrical projection.

11. (Currently Amended): A semiconductor device comprising:  
a capacitor formed above a semiconductor substrate and including  
a cylindrical-shaped storage electrode having a cylindrical projection, an edge of the  
cylindrical projection being located on an uppermost part of the cylindrical-shaped storage electrode,  
a capacitor dielectric film formed on the storage electrode, and  
a plate electrode formed on the capacitor dielectric film,  
the cylindrical-shaped storage electrode being formed of a metal film and ~~an upper cylinder~~  
~~edge of the storage electrode~~ the edge of the cylindrical projection being rounded.

12. (Currently Amended): A semiconductor device according to claim 11, wherein

the cylindrical-shaped storage electrode has a thickness gradually thickened toward to the upper

$\beta'$  ~~cylinder edge~~ the edge of the cylindrical projection.

13-20. (Withdrawn)

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